



### 100V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	BVDSS RDS(ON)		I <sub>D</sub> T <sub>C</sub> = +25°C	
100V	$9.5 \text{m}\Omega @V_{GS} = 10V$	TO220AB	98A	

## **Description**

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

# **Applications**

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

## **Features**

- Low Input Capacitance
- High BV<sub>DSS</sub> Rating for Power Application
- Low Input/Output Leakage
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

### **Mechanical Data**

- Case: TO220AB
- Through Hole Package
- Max Soldering Temperature +260°C for 30 Seconds as per JEDEC J-STD-020
- Case Material: Molded Plastic, UL Flammability Rating 94V-0
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 2.24 grams (Approximate)

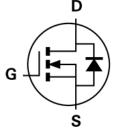




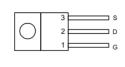




Bottom View



Equivalent Circuit



Top View Pin Out Configuration

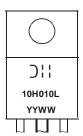
### **Ordering Information (Note 4)**

r.		
Part Number	Case	Packaging
DMT10H010LCT	TO220AB	50 Pieces/Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



DMT10H010LCT Document number: DS37976 Rev. 6 - 2





# Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	100	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	lD	98 62	А
Maximum Continuous Body Diode Forward Current	T <sub>C</sub> = +25°C	Is	90	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	92	Α
Avalanche Current, L = 0.3mH (Note 7)	I <sub>AS</sub>	10	Α	
Avalanche Energy, L = 0.3mH (Note 7)		Eas	15	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	2	W
Thermal Resistance, Junction to Ambient (Note 5)		Reja	61	°C/W
Total Power Dissipation	Tc = +25°C	PD	139	W
Thermal Resistance, Junction to Case		Rejc	0.9	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BVDSS	100	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.4	1.9	3.0	٧	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
		_	6.9	9.5		V <sub>G</sub> S = 10V, I <sub>D</sub> = 13A	
Static Drain-Source On-Resistance	RDS(ON)		8	12	mΩ	Vgs = 6V, ID = 13A	
	-(- )	_	10	20		$V_{GS} = 4.5V, I_{D} = 5A$	
Diode Forward Voltage	VsD	_	0.8	1.3	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 13A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	_	4166	_		V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss	_	764	_	pF		
Reverse Transfer Capacitance	Crss	1	44	1		1 - 1101112	
Gate Resistance	Rg		2		Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	QG	_	58.4	_		V 50V L 40A	
Gate-Source Charge	Qgs	_	11.4	_	nC	V <sub>DD</sub> = 50V, I <sub>D</sub> = 13A, V <sub>GS</sub> = 10V	
Gate-Drain Charge	$Q_{GD}$	_	14.2	_			
Turn-On Delay Time	td(ON)	_	11.6	_		$V_{DD} = 50V, V_{GS} = 10V,$ $I_{D} = 13A, R_{G} = 6\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	14.1	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	42.9	_	ns		
Turn-Off Fall Time	tF	_	22	_			
Reverse Recovery Time	trr	_	49.8	_	ns	1 424 4:/4+ 4004/	
Reverse Recovery Charge	Qrr	_	85.1	_	nC	F = 13A, di/dt = 100A/μs	

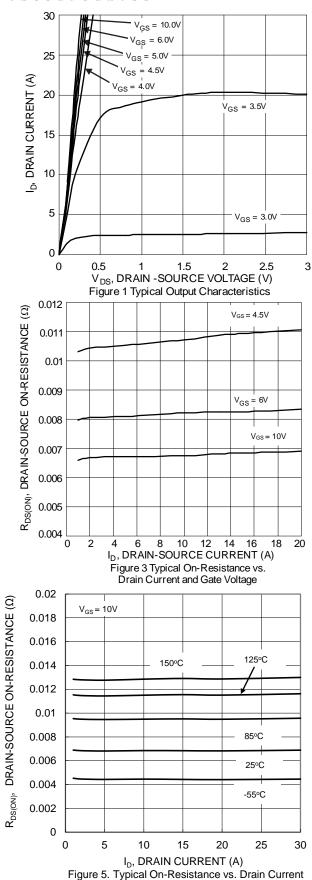
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

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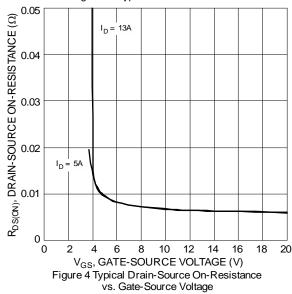
<sup>6.</sup> Short duration pulse test used to minimize self-heating effect. 7. Guaranteed by design. Not subject to product testing.







30  $V_{DS} = 5V$ 25 ID, DRAIN CURRENT (A) 20 15 10 85°C 150°C 5 25°C 125°C -55°C 0 2 6 1 3 5 V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



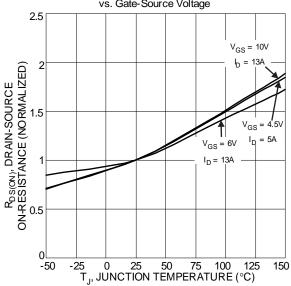
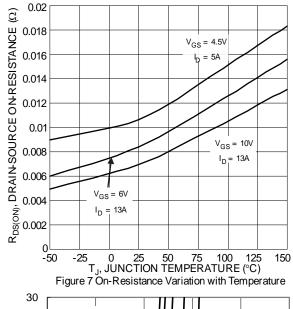


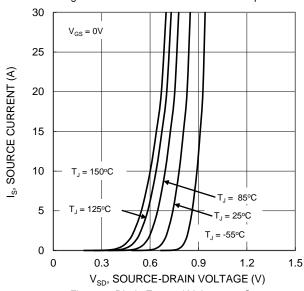
Figure 6 On-Resistance Variation with Temperature

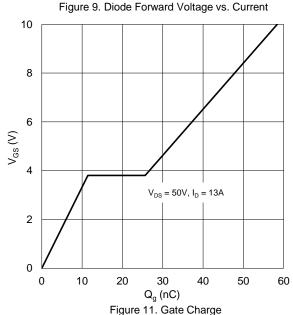
and Junction Temperature

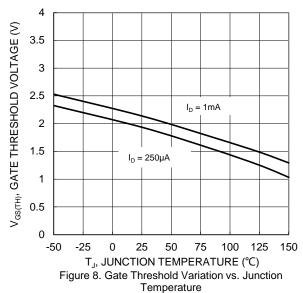


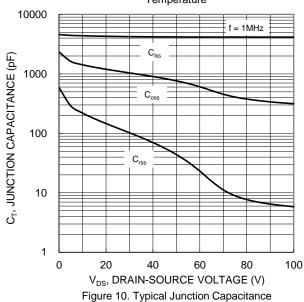


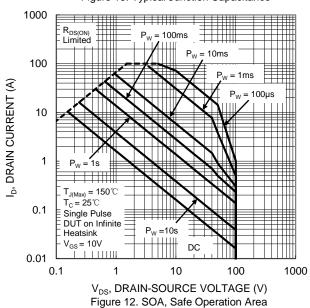














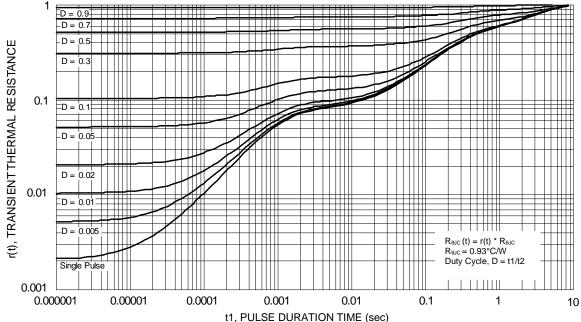


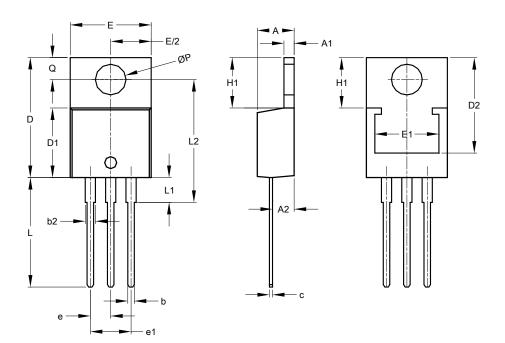
Figure 13 Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **TO220AB**



TO220AB						
Dim	Min	Max	Тур			
Α	3.56	4.82	-			
<b>A</b> 1	0.51	1.39	-			
A2	2.04	2.92	-			
b	0.39	1.01	0.81			
b2	1.15	1.77	1.24			
С	0.356	0.61	-			
D	14.22	16.51	-			
D1	8.39	9.01	-			
D2	11.45	12.87	-			
е	-	-	2.54			
e1	-	-	5.08			
E	9.66	10.66	-			
E1	6.86	8.89	-			
H1	5.85	6.85	-			
L	12.70	14.73	-			
L1	-	4.42	-			
L2	15.80	17.51	16.00			
Р	3.54	4.08	-			
Q	2.54	3.42	-			
All	All Dimensions in mm					



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